

## **GaAs MMIC Low Noise Amplifier Chip, 10-13GHz**

### **Performance characteristics**

- Frequency range:10-13GHz
- Small signal gain: 22.5dB
- Gain flatness:  $\pm 0.5$ dB
- Noise figure:0.85dB
- P-1dB: 12.5dBm
- Power supply:+5V/50mA
- Input/Output: 50Ohm
- 100% on-chip testing
- Chip size: 1.48 x 0.82 x 0.1 mm

### **Product Introduction**

GLA-1013B is a broadband low-noise amplifier chip with a frequency range of 10GHz~13GHz, a small signal gain of 22.5dB, and an in band noise figure of 0.85dB. GLA-1013B adopts a+5V single power supply with a current of 50mA.

#### **Use restriction parameters<sup>1</sup>**

Maximum leakage voltage	+7V
Maximum input power	+20dBm
Working temperature	-55 ~ +85°C
Storage temperature	-65 ~ +150°C

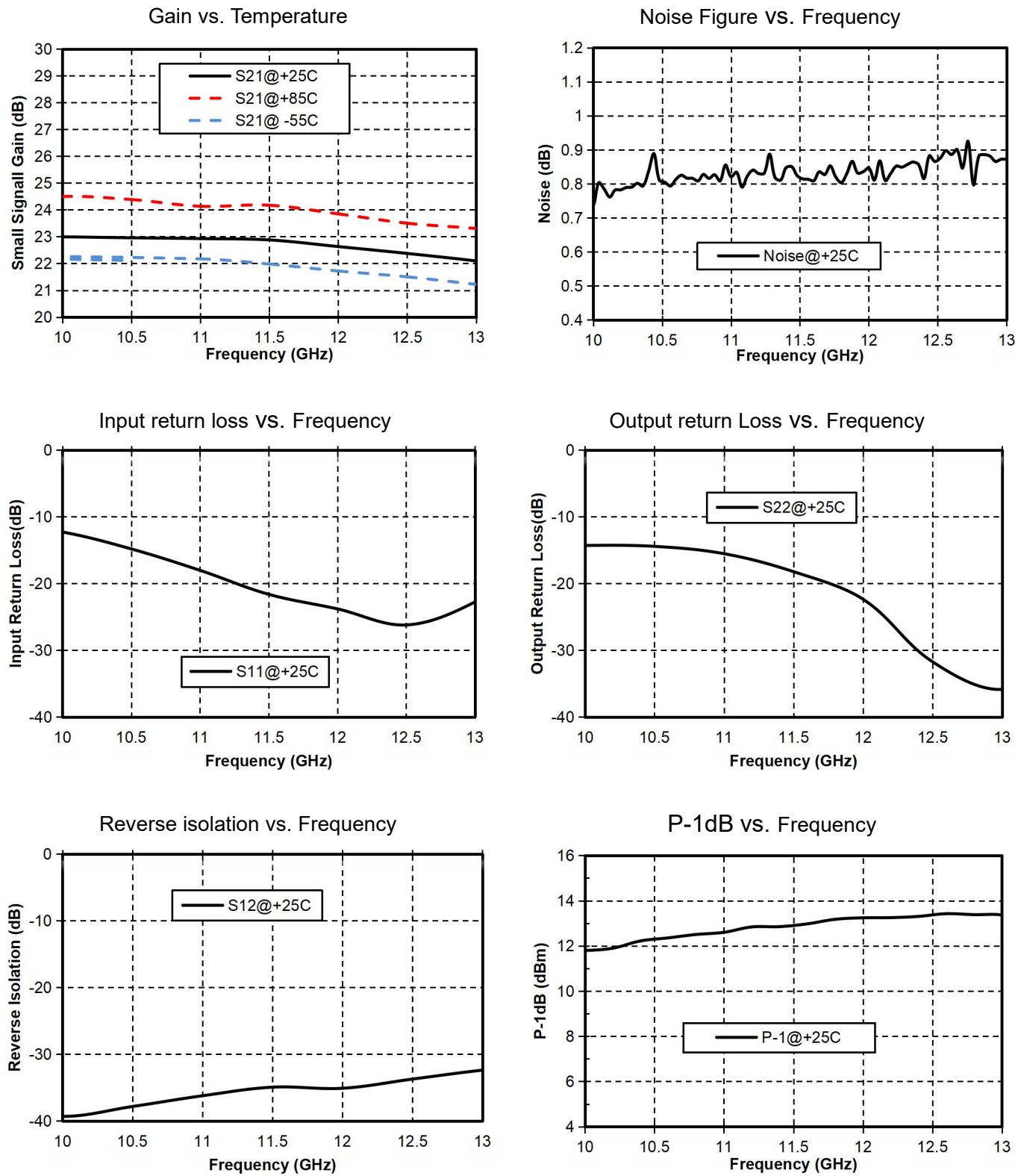
**【1】** Exceeding any of the above maximum limits may result in permanent damage.

#### **Electrical performance parameters( $T_A = +25^\circ\text{C}$ , $Vd=+5\text{V}$ )**

Index	Minimum value	Typical value	Maximum value	Unit
Frequency range		10-13		GHz
Small signal gain	-	22.5	-	dB
Gain flatness		$\pm 0.5$		dB
Noise figure	-	0.85	-	dB
P-1dB	-	12.5	-	dBm
Psat		13.5		dBm
Input return loss	-	19	-	dB
Output return Loss	-	21	-	dB
Static current		50		mA

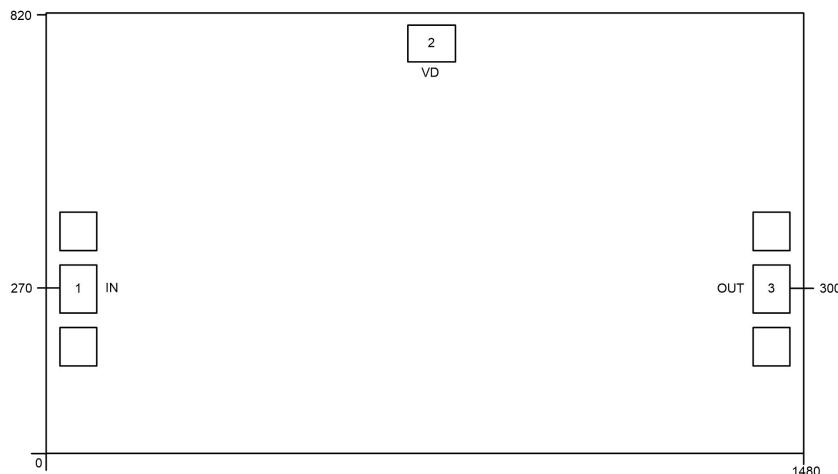
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### Main indicator testing curve



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### External structure<sup>2</sup>



【2】The units in the figure are all millimeters, with a tolerance of  $\pm 100\mu\text{m}$ .

### Definition of bonding pressure point

Bond point number	Functional symbols	Function Description
1	RFIN	RF signal input terminal, no need for DC capacitors.
3	RFOUT	RF signal output terminal, no need for DC isolation capacitor.
2	VDD	Amplifier drain bias, requires an external 100pF bypass capacitor.
Chip bottom	GND	The bottom of the chip needs to be well grounded with RF and DC.

### Recommended assembly diagram

